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Abstract of the Disclosure

Disclosed is a manufacturing method of a semiconductor device which comprises which comprises an element isolation region formation step; a side wall formation step; a diffusion layer formation step; an activation step; a silicide formation step; and a removing The element isolation region formation step is the one for forming a field oxide film on a semiconductor substrate to form an element isolation region. In order to form a diffusion layer by introducing impurities into the semiconductor substrate, after injecting the fluorides (ion injection species) of elements into the semiconductor substrate, a thermal treatment is performed at a lower temperature than that of a thermal treatment for activating the diffusion layer prior to the activation of the diffusion layer, and fluorine produced from the ion injection species is discharged to the outside.

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